Amendments to the Claims:

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:

depositing a diffusion barrier layer, a metal layer and an anti reflection layer on a semiconductor substrate;

depositing an insulating film on the anti reflection layer;

depositing and patterning a photosensitive material on the insulating film;

etching portions of the insulating film, the anti reflection layer and the metal layer using activated plasma and the photosensitive material as a mask, whereby a portions of side walls of the metal layer are over-etched by plasma ions;

removing the photosensitive material;

forming a side wall oxide film on the over-etched side walls of the metal layer by reacting the metal layer with ozone; and

etching portions of the diffusion barrier layer using the insulating film and the side wall oxide film as an etch mask.

2. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the metal layer is made of aluminum (Al).

3. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the diffusion barrier layer is made of Ti/TiN layer, and the anti reflection layer is made of Ti/TiN layer, and the side wall oxide film is an Al_2O_3 film.

4. (Currently Amended) A method of forming a metal line in a semiconductor memory device according to claim 1, wherein ~~the~~ the anti reflection layer, the metal layer and the diffusion barrier layer are dry-etched using activated plasma comprising $Cl_2/BCl_3/N_2$ gas.

5. (Canceled)

6. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is a nitride film.

7. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of CHF_3/CF_4/Ar or C_xF_y (where x, y are natural numbers)/O_2/Ar gas.

8. (Canceled)

9. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:

depositing a first, second and third conductive layers on a semiconductor substrate;

depositing an insulating film on the third conductive layer;

dry etching portions of the insulating film, the third and the second conductive layers using activated plasma, whereby a portions of side walls of the second conductive layer are over-etched by plasma ions;

forming a side wall oxide film on the side walls of the over-etched second conductive layer by reacting the second conductive layer with ozone; and

etching portions of the first conductive layer using the insulating film and the side wall oxide film as an etch mask.

10. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the first conductive layer is made of Ti/TiN layer, the second conductive layer is made of aluminum (Al), and the third conductive layer is made of Ti/TiN layer.

11. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the side wall oxide film is an Al_2O_3 film.

12. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is a nitride film.

13. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $CHF_3/CF_4/Ar$ or C_xF_y (where x, y are natural numbers)/O_2/Ar gas.

14. (Previously Presented) A method of forming a metal line in a semiconductor memory device according to claim 9, wherein the third and second conductive layers are dry-etched using activated plasma comprising $Cl_2/BCl_3/N_2$ gas.